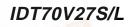
查询IDT70V27L15BF供应商

捷多邦,专业PCB打样工厂,24小时加急出货



HIGH-SPEED 3.3V 32K x 16 DUAL-PORT STATIC RAM

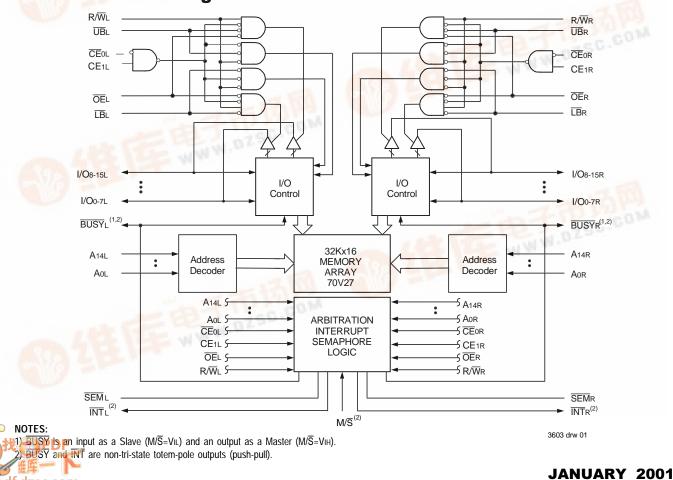


Features:

- True Dual-Ported memory cells which allow simultaneous access of the same memory location
- High-speed access
- Industrial: 35ns (max.)
 - Commercial: 15/20/25/35/55ns (max.)
- Low-power operation
 - IDT70V27S
 - Active: 500mW (typ.) Standby: 3.3mW (typ.)
 - IDT70V27L Active: 500mW (typ.) Standby: 660µW (typ.)
- Separate upper-byte and lower-byte control for bus matching capability
- Dual chip enables allow for depth expansion without external logic

Functional Block Diagram

- IDT70V27 easily expands data bus width to 32 bits or more using the Master/Slave select when cascading more than one device
- M/S = VIH for BUSY output flag on Master, M/S = VIL for BUSY input on Slave
- Busy and Interrupt Flags
- On-chip port arbitration logic
- Full on-chip hardware support of semaphore signaling between ports
- Fully asynchronous operation from either port
- LVTTL-compatible, single 3.3V (±0.3V) power supply
- Available in 100-pin Thin Quad Flatpack (TQFP), 108-pin Ceramic Pin Grid Array (PGA), and 144-pin Fine Pitch BGA (fpBGA)
- Industrial temperature range (-40°C to +85°C) is available for selected speeds



Description:

The IDT70V27 is a high-speed 32K x 16 Dual-Port Static RAM, designed to be used as a stand-alone 512K-bit Dual-Port RAM or as a combination MASTER/SLAVE Dual-Port RAM for 32-bit and wider word systems. Using the IDT MASTER/SLAVE Dual-Port RAM approach in 32-bit or wider memory system applications results in full-speed, error-free operation without the need for additional discrete logic.

The device provides two independent ports with separate control, address, and I/O pins that permit independent, asynchronous access for

Commercial and Industrial Temperature Range

reads or writes to any location in memory. An automatic power down feature controlled by the chip enables (\overline{CE}_0 and CE_1) permits the on-chip circuitry of each port to enter a very low standby power mode.

Fabricated using IDT's CMOS high-performance technology, these devices typically operate on only 500mW of power. The IDT70V27 is packaged in a 100-pin Thin Quad Flatpack (TQFP), a 108-pin ceramic Pin Grid Array (PGA), and a 144-pin Fine Pitch BGA (fp BGA).

INDEX BUS <u>INT</u>R AOR ☐ A2R ☐ A3R A4R ☐ A5R A5R A7R A1R A8R A3L A6I A5L A2L 100 99 98 97 96 95 94 93 92 91 90 89 88 87 86 85 84 83 82 81 80 79 78 77 76 75 A9L A9R A10R A10L C 74 A11L □ 3 A11R 73 A12L A12R 72 A13L ⊏ A13R 71 A14L ⊏ A14R 70 NC ⊏ NC 69 NC ⊐ NC 18 68 NC NC 19 67 ⊐ <u>L</u>Br 66 IDT70V27PF ⊐ ŪBr 65 PN100-1⁽⁴⁾ $\Box \overline{CE}OR$ 64 CE1L -13 CE1R 63 100-PIN TOFP SEMR 14 TOP VIEW⁽⁵⁾ 62 GND 61 R/WR 60 **1**17 ŌĒr 59 ⊐ GND 58 GND 19 GND 57 I/O15L = 20 ⊐ I/O15R 56 I/O14L □ 21 55 ⊐ I/O14R I/O13L 22 54 □ **I/O**13R I/O12L 23 53 ⊐ I/O12R I/O11L 52 □ I/O11R 124 I/O10L 51 □ I/O10R 25 50 3603 drw 02

Pin Configurations^(1,2,3)

NOTES:

- 1. All Vcc pins must be connected to power supply.
- 2. All GND pins must be connected to ground supply.
- 3. Package body is approximately 14mm x 14mm x 1.4mm.
- 4. This package code is used to reference the package diagram.
- 5. This text does not indicate orientation of the actual part-marking.

Commercial and Industrial Temperature Range

3603 drw 02a

Pin Configurations^(1,2,3) (con't.)

			•									
A1	A2	A3	A4	A5	A6	A7	A8	A9	A10	A11	A12	A13
NC	NC	A8L	A5L	A1L	INTL	GND	BUSYR	A1R	A5R	NC	NC	NC
B1	B2	B3	B4	B5	B6	B7	B8	B9	B10	B11	B12	B13
NC	NC	NC	A6L	A2L	NC	M/S	ĪNTR	A2R	A6R	NC	NC	NC
C1	C2	C3	C4	C5	C6	C7	C8	C9	C10	C11	C12	C13
A10L	A9L	NC	A7L	АзL	NC	NC	NC	Азr	A7R	A9R	A10R	A11R
D1	D2	D3	D4	D5	D6	D7	D8	D9	D10	D11	D12	D13
A14L	A13L	A12L	A11L	A4L	Aol	BUSYL	AOR	A4R	A8R	A12R	A13R	A14R
E1	E2	E3	E4					1	E10	E11	E12	E13
LBL	NC	NC	NC						NC	NC	NC	LBR
F1	F2	F3	F4	1					F10	F11	F12	F13
SEML	CE1L	CEOL	ŪBL		ID.	T70V27	BF	UBR		CE1R	SEMR	
G1	G2	G3	G4	1	В	F144-1 ⁽	4)		G10	G11	G12	G13
Vcc	Vcc	Vcc	NC		144	-Pin fpB	GA		NC	NC	GND	GND
H1	H2	НЗ	H4	1	Т	op View	(5)		H10	H11	H12	H13
NC	R/WL	ŌĒL	NC						NC	ŌĒR	R/WR	GND
J1	J2	J3	J4	1					J10	J11	J12	J13
GND	I/O15L	I/O14L	I/013L						I/O13R	I/O14R	I/O15R	GND
K1	K2	K3	K4	K5	K6	K7	K8	K9	K10	K11	K12	K13
I/O12L	NC	NC	NC	I/O6L	I/O3L	I/O0R	I/O3R	I/O6R	I/O11R	NC	NC	I/O12R
L1	L2	L3	L4	L5	L6	L7	L8	L9	L10	L11	L12	L13
I/O11L	I/O10L	NC	NC	I/O5L	I/O _{2L}	GND	Vcc	I/O5R	NC	NC	NC	I/O10R
M1	M2	МЗ	M4	M5	M6	M7	M8	M9	M10	M11	M12	M13
I/O9L	NC	NC	Vcc	I/O4L	GND	I/Ool	I/O2R	I/O4R	I/O7R	I/O8R	NC	I/O9R
N1 NC	N2 NC	N3 I/O8L	N4 I/O7L	N5 NC	N6 I/O1L	N7 VCC	N8 I/O1R	N9 NC	N10 VCC	N11 NC	N12 NC	N13 NC

NOTES:

All Vcc pins must be connected to power supply.
 All GND pins must be connected to ground supply.
 Package body is approximately 12mm x 12mm x 1.4mm.
 This package code is used to reference the package diagram.
 This text does not indicate orientation of the actual part-marking.

Commercial and Industrial Temperature Range

Pin Configurations^(1,2,3) (con't.)

ngai	auv	13			,							
	81	80	77	74	72	69	68	65	63	60	57	54
12	A10R	A11R	A14R	NC	UBR	SEMR	GND	GND	NC	I/O13R	I/O10R	NC
	84	83	78	76	73	70	67	64	61	59	56	53
11	A7R	A8R	A13R	NC	LBR	CE1R	R/WR	GND	I/O14R	I/O12R	I/O9r	NC
	87	86	82	79	75	71	66	62	58	55	51	50
10	A4R	A5R	A9R	A12R	NC	CEOR	ŌĒR	I/O15R	I/O11R	NC	I/O8R	I/O7r
	90	88	85							52	49	47
09	A1R	Азr	A6R							NC	Vcc	I/O5R
	92	91	89							48	46	45
08	ĪNTR	AOR	A2R					I/O6R	I/O4R	I/O3R		
	95	94	93					44	43	42		
07	GND	M/S	BUSYR			IDT7 G10		I/O2R	I/O1R	I/O0R		
	96	97	98							39	40	41
06	BUSYL	INTL	NC				IN PGA √IEW ⁽⁵⁾			I/O1L	I/Ool	GND
	99	100	102							35	37	38
05	Aol	A1L	A3L							I/O4L	I/O2L	GND
	101	103	106	1						31	34	36
04	A2L	A4L	A7L							Vcc	I/O5L	I/O3L
	104	105	1	4	8	12	17	21	25	28	32	33
03	A5L	A6L	A10L	A13L	NC	CE1L	GND	I/O14L	I/O10L	NC	I/O7L	I/O6L
	107	2	5	7	10	13	16	19	22	24	29	30
02	A8L	A11L	A14L	NC	UBL	SEML	ŌĒL	GND	I/O13L	I/O11L	NC	I/O8L
	108	3	6	9	11	14	15	18	20	23	26	27
01	A9L	A12L	NC	LBL	CEOL	Vcc	R/WL	NC	I/O15L	I/O12L	I/O9L	NC
1	A	В	С	D	E	F	G	н	J	к	L	М
												3603 drw (
INDEX												

NOTES:

- 1. All Vcc pins must be connected to power supply.
- 2. All GND pins must be connected to ground supply.

- Package body is approximately 1.21in x 1.21in x 1.6in.
 This package code is used to reference the package diagram.
- 5. This text does not indicate orientation of the actual part-marking.

Pin Names

Left Port	Right Port	Names
\overline{CE} OL, CE1L	\overline{CE} OR, CE1R	Chip Enable
R/WL	R/Wr	Read/Write Enable
ŌĒL	ŌĒR	Output Enable
Aol - A14l	A0R - A14R	Address
1/Ool - 1/O15l	I/Oor - I/O15r	Data Input/Output
SEML	SEMR	Semaphore Enable
ŪBL	ŪBR	Upper Byte Select
L BL	LB R	Lower Byte Select
ĪNTL	INTR	Interrupt Flag
BUSYL	BUSYR	Busy Flag
M	/ S	Master or Slave Select
V	CC	Power
G	ND	Ground

Truth Table I – Chip Enable^(1,2,3)

CE	CE₀	CE1	Mode				
	Vil	Vін	Port Selected (TTL Active)				
L	≤ 0.2V	≥Vcc -0.2V	Port Selected (CMOS Active)				
	ViH	Х	Port Deselected (TTL Inactive)				
	Х	ViL	Port Deselected (TTL Inactive) Port Deselected (TTL Inactive)				
Н	≥Vcc -0.2V	Х	Port Deselected (CMOS Inactive)				
	Х	<u>≤</u> 0.2V	Port Deselected (CMOS Inactive)				
NOTES			3603 tbl 02				

NOTES:

1. Chip Enable references are shown above with the actual \overline{CE}_0 and CE_1 levels, \overline{CE} is a reference only.

2. Port "A" and "B" references are located where \overline{CE} is used.

3. "H" = VIH and "L" = VIL

Truth Table II – Non-Contention Read/Write Control

		Inpu	uts ⁽¹⁾			Out	puts	
CE ⁽²⁾	R/₩	ŌĒ	ŪB	LB	SEM	I/O8-15	I/O0-7	Mode
Н	Х	Х	Х	Х	Н	High-Z	High-Z	Deselected: Power-Down
Х	Х	Х	Н	Н	Н	High-Z	High-Z	Both Bytes Deselected
L	L	Х	L	Н	Н	DATAIN	High-Z	Write to Upper Byte Only
L	L	Х	Н	L	Н	High-Z	DATAIN	Write to Lower Byte Only
L	L	Х	L	L	Н	DATAIN	DATAIN	Write to Both Bytes
L	Н	L	L	Н	Н	DATAOUT	High-Z	Read Upper Byte Only
L	Н	L	Н	L	Н	High-Z	DATAOUT	Read Lower Byte Only
L	Н	L	L	L	Н	DATAOUT	DATAOUT	Read Both Bytes
Х	Х	Н	Х	Х	Х	High-Z	High-Z	Outputs Disabled

NOTES:

1. AoL — A14L \neq AoR — A14R. 2. Refer to Chip Enable Truth Table.

Truth Table III – Semaphore Read/Write Control

		Inpu	uts ⁽¹⁾			Out	puts	
CE ⁽²⁾	R/W	ŌĒ	ŪB	LB	SEM	I/O8-15	I/O0-7	Mode
Н	Н	L	Х	Х	L	DATAOUT	DATAOUT	Read Data in Semaphore Flag
Х	Н	L	Н	Н	L	DATAOUT	Read Data in Semaphore Flag	
Н	\uparrow	Х	Х	Х	L	DATAIN	DATAIN	Write I/Oo into Semaphore Flag
Х	\uparrow	Х	Н	Н	L	DATAIN	DATAIN	Write I/Oo into Semaphore Flag
L	Х	Х	L	Х	L			Not Allowed
L	Х	Х	Х	L	L			Not Allowed

3603 tbl 04

3603 tbl 03

5

Absolute Maximum Ratings⁽¹⁾

Symbol	Rating	Commercial & Industrial	Unit
Vterm ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +4.6	V
Tbias	Temperature Under Bias	-55 to +125	٥C
Tstg	Storage Temperature	-65 to +150	٥C
lout	DC Output Current	50	mA

NOTES:

- 1. Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
- 2. VTERM must not exceed Vcc + 0.3V for more than 25% of the cycle time or 10ns maximum, and is limited to \leq 20mA for the period of VTERM \geq VCC + 0.3V.

Capacitance⁽¹⁾ (TA = +25°C, f = 1.0mhz)TQFP ONLY

Symbol	Parameter	Conditions ⁽²⁾	Max.	Unit
Cin	Input Capacitance	ViN = 3dV	9	pF
Соит	Output Capacitance	Vout = 3dV	10	pF
				3603 tbl 08

NOTES:

1. This parameter is determined by device characterization but is not production tested.

2. 3dV represents the interpolated capacitance when the input and output signals switch from 0V to 3V or from 3V to 0V.

VIL Input Low Voltage -0.3(1)

3603 tbl 05

NOTES:

1. VIL \geq -1.5V for pulse width less than 10ns.

Parameter

Supply Voltage

Input High Voltage

Ground

2. VTERM must not exceed Vcc + 0.3V.

Conditions⁽¹⁾

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range (Vcc = 3.3V ± 0.3V)

			70V	27S	70V	27L	
Symbol	Parameter	Test Conditions	Min.	Max.	Min.	Мах.	Unit
Lu	Input Leakage Current ⁽¹⁾	Vcc = 3.6V, VIN = 0V to Vcc	-	10	-	5	μA
I lo	Output Leakage Current	\overline{CE} = VIH, VOUT = 0V to VCC	_	10	_	5	μA
Vol	Output Low Voltage	Iol = 4mA	-	0.4	-	0.4	V
Vон	Output High Voltage	IOH = -4mA	2.4	-	2.4	_	V

NOTE:

1. At Vcc \leq 2.0V, input leakages are undefined.

Commercial and Industrial Temperature Range

Maximum Operating Temperature and Supply Voltage(1,2)

Grade	Ambient Temperature	GND	Vcc
Commercial	0°C to +70°C	0V	3.3V <u>+</u> 0.3V
Industrial	-40°C to +85°C	0V	3.3V <u>+</u> 0.3V
	-		3603 tbl 06

NOTES:

1. This is the parameter TA. This is the "instant on" case temperature.

Recommended DC Operating

2. Industrial temperature: for specific speeds, packages and powers contact your sales office.

Min.

3.0

0

2.0

Typ.

3.3

0

_

Max.

3.6

0 VCC+0.3V⁽²⁾

0.8

Unit

V

٧

V

V

3603 tbl 07

L					
-	_	_	_	-	

Symbol

Vcc

GND

V⊪

3603 tbl 09

Commercial and Industrial Temperature Range

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range^(1,6,7) (Vcc = 3.3V ± 0.3V)

					70V27X15 Com'l Only		70V2 Com'l		70V27X25 Com'l Only		
Symbol	Parameter	Test Condition	Versi	on	Typ. ⁽²⁾	Мах.	Тур. ⁽²⁾	Мах.	Тур. ⁽²⁾	Max.	Unit
ICC	Dynamic Operating Current	\overline{CE} = VIL, Outputs Disabled SEM = VIH	COM'L	S L	170 170	260 225	165 165	255 220	145 145	245 210	mA
	(Both Ports Active)	$f = fMAX^{(3)}$	IND'L	S L					145 145	280 245	
ISB1	Standby Current (Both Ports - TTL Level	$\overline{CE}_{L} = \overline{CE}_{R} = V_{IH}$ $\overline{SEM}_{R} = \overline{SEM}_{L} = V_{IH}$	COM'L	S L	44 44	70 60	39 39	60 50	27 27	50 40	mA
	Inputs) f = fMAX ⁽³⁾ IND'L Standby Current $\overline{CE'A^*} = VIL$ and $\overline{CE'B^*} = VIH^{(5)}$ COM'L	S L					27 27	60 50			
ISB2	Standby Current (One Port - TTL Level Inputs)	$\overline{C}\overline{E}^{*}A^{*} = VIL$ and $\overline{C}\overline{E}^{*}B^{*} = VIH^{(5)}$ Active Port Outputs Disabled, $f=f_{MAX}^{(3)}$	COM'L	S L	115 115	160 145	105 105	155 140	90 90	150 135	mA
		$\frac{\text{T=TMAX}^{(3)}}{\text{SEMR}} = \overline{\text{SEML}} = \text{Vih}$	IND'L	S L					90 90	170	
ISB3	Full Standby Current (Both Ports - All CMOS Level Inputs)	Both Ports $\overline{CE}L$ and $\overline{CE}R \ge Vcc - 0.2V$ $VN \ge Vcc - 0.2V$ or	COM'L	S L	1.0 0.2	6 3	1.0 0.2	6 3	1.0 0.2	6 3	mA
	Civios Level inpuis)	$\frac{V_{IN} \leq 0.2V, f = 0^{(4)}}{\overline{SEMR} = \overline{SEML} \geq VCC - 0.2V}$	IND'L	S L					1.0 0.2	10 6	
ISB4	Full Standby Current (One Port - All CMOS	$\frac{\overline{C}\overline{E}^{*}A^{*}}{\overline{C}\overline{E}^{*}B^{*}} \ge Vcc + 0.2V^{(5)}$	COM'L	S L	115 115	155 140	105 105	150 135	90 90	145 130	mA
Level Inputs)	revet inbrie	ts) $\begin{array}{l} \overline{\text{SEMR}} = \overline{\text{SEML}} \geq \text{Vcc} - 0.2\text{V} \\ \overline{\text{VN}} \geq \text{Vcc} - 0.2\text{V} \text{ or } \overline{\text{VN}} \leq 0.2\text{V} \\ \text{Active Port Outputs Disabled} \\ f = f_{\text{MAX}^{(3)}} \end{array}$		S L					90 90	170 145	

NOTES:

3. At f = fMAX, address and control lines (except Output Enable) are cycling at the maximum frequency read cycle of 1/tRc, and using "AC Test Conditions" of input levels of GND to 3V.

4. f = 0 means no address or control lines change.

5. Port "A" may be either left or right port. Port "B" is the opposite from port "A".

6. Refer to Chip Enable Truth Table.

7. Industrial temperature: for other speeds, packages and powers contact your sales office.

^{1. &#}x27;X' in part numbers indicates power rating (S or L).

^{2.} Vcc = 3.3V, TA = +25°C, and are not production tested. Icccc = 90mA (Typ.)

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range^(1,6,7) (Vcc = 3.3V ± 0.3V)

					7X35 & Ind	70V27X55 Com'l Only		
Symbol	Parameter	Test Condition	Version	Typ. ⁽²⁾	Мах.	Тур. ⁽²⁾	Мах.	Unit
ICC	Dynamic Operating Current (Both Ports Active)	$\overline{CE} = V_{IL}, Outputs Disabled$ $\overline{SEM} = V_{IH}$	COM'L S		235 190	125 125	225 180	mA
		$f = f_{MAX}^{(3)}$	IND'L S		270 235	125 125	260 225	
ISB1	Standby Current (Both Ports - TTL Level	$\overline{CEL} = \overline{CER} = VH$ $\overline{SEMR} = \overline{SEML} = VH$	COM'L S		45 35	15 15	40 30	mA
	Inputs)	$f = f_{MAX}^{(3)}$	IND'L S		55 45	15 15	50 40	
ISB2	Standby Current (One Port - TTL Level Inputs)	$\overline{CE}^{*}A^{*} = VIL \text{ and } \overline{CE}^{*}B^{*} = VIH^{(5)}$ Active Port Outputs Disabled,	COM'L S		140 125	75 75	140 125	mA
		$\frac{f=f_{MAX}^{(3)}}{\overline{SEM}R} = \overline{SEM}L = VIH$	IND'L S		160 140	75 75	160 140	
ISB3	Full Standby Current (Both Ports - All CMOS Level Inputs)	Both Ports CEL and CER ≥ Vcc - 0.2V Vii > Vcc - 0.2V or	COM'L S		6 3	1.0 0.2	6 3	mA
	inputs)	$\frac{V_{IN} \leq 0.2V, f = 0^{(4)}}{\overline{SEM}R = \overline{SEM}L \geq VCC - 0.2V}$	IND'L S		10 6	1.0 0.2	10 6	
ISB4	Full Standby Current (One Port - All CMOS Level Inputs)		COM'L S		135 120	75 75	135 120	mA
		SEIVIR = SEIVIL \geq VCC - 0.2V VIN \geq VCC - 0.2V or VIN \leq 0.2V Active Port Outputs Disabled f = fMAX ⁽³⁾	IND'L S		160 135	75 75	160 135	

NOTES:

1. 'X' in part numbers indicates power rating (S or L).

2. Vcc = 3.3V, TA = $+25^{\circ}C$, and are not production tested. Icccc = 90mA (Typ.)

3. At f = fmax, address and control lines (except Output Enable) are cycling at the maximum frequency read cycle of 1/tRc, and using "AC Test Conditions" of input levels of GND to 3V.

4. f = 0 means no address or control lines change.

5. Port "A" may be either left or right port. Port "B" is the opposite from port "A".

6. Refer to Chip Enable Truth Table.

7. Industrial temperature: for other speeds, packages and powers contact your sales office.

AC Test Conditions

Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	5ns Max.
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
Output Load	Figures 1 and 2
	3603 tbl 11

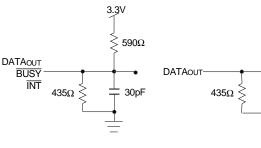
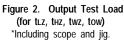


Figure 1. AC Output Test Load



3.3V

590Ω

5pF

3603 drw 04

3603 thl 10b

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range^(4, 6)

		70V27X15 Com'l Only			27X20 I Only	70V27X25 Com'l Only		
Symbol	Parameter	Min.	Мах.	Min.	Мах.	Min.	Мах.	Unit
READ CYC	CLE							
trc	Read Cycle Time	15	_	20		25	_	ns
tAA	Address Access Time		15		20		25	ns
t ACE	Chip Enable Access Time ⁽³⁾		15		20		25	ns
t abe	Byte Enable Access Time ⁽³⁾		15		20		25	ns
t AOE	Output Enable Access Time		10		12		15	ns
tон	Output Hold from Address Change	3	_	3		3	_	ns
tLZ	Output Low-Z Time ^(1,2)	3		3		3		ns
tHZ	Output High-Z Time ^(1,2)		12		12		15	ns
t₽U	Chip Enable to Power Up Time ^(2,5)	0	_	0		0		ns
tPD	Chip Disable to Power Down Time ^(2,5)		15		20		25	ns
tSOP	Semaphore Flag Update Pulse (OE or SEM)	10		10		15		ns
tsaa	Semaphore Address Access Time		15		20		35	ns
							36	603 tbl 12a
		701/2	17V2E	701/0				

		70V27X35 Com'l & Ind		70V27X55 Com'l Only		
Symbol	Parameter	Min.	Мах.	Min.	Мах.	Unit
READ CYC	CLE					
tRC	Read Cycle Time	35		55		ns
taa	Address Access Time		35		55	ns
t ACE	Chip Enable Access Time ⁽³⁾		35		55	ns
t ABE	Byte Enable Access Time ⁽³⁾		35		55	ns
taoe	Output Enable Access Time		20		30	ns
tон	Output Hold from Address Change	3		3		ns
t∟z	Output Low-Z Time ^(1,2)	3		3		ns
tHZ	Output High-Z Time ^(1,2)		20		25	ns
t₽U	Chip Enable to Power Up Time ^(2,5)	0		0	_	ns
tPD	Chip Disable to Power Down Time ^(2,5)		45		50	ns
tSOP	Semaphore Flag Update Pulse (OE or SEM)	15		15		ns
tsaa	Semaphore Address Access Time		45		65	ns

NOTES:

1. Transition is measured 0mV from Low or High-impedance voltage with Output Test Load (Figure 2).

2. This parameter is guaranteed by device characterization, but is not production tested. 3. To access RAM, $\overline{CE} = V_{IL}$ and $\overline{SEM} = V_{IH}$. To access semaphore, $\overline{CE} = V_{IH}$ and $\overline{SEM} = V_{IL}$.

4. 'X' in part numbers indicates power rating (S or L).

5. Refer to Chip Enable Truth Table.

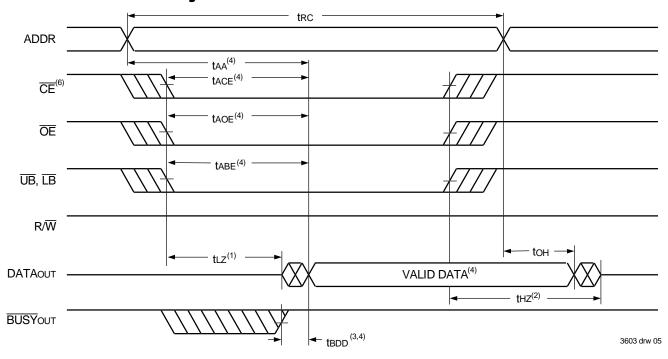
6. Industrial temperature: for other speeds, packages and powers contact your sales office.

3603 tbl 12b

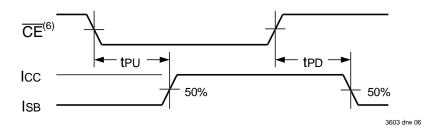
High-Speed 3.3V 32K x 16 Dual-Port Static RAM

Commercial and Industrial Temperature Range

Waveform of Read Cycles⁽⁵⁾



Timing of Power-Up Power-Down



NOTES:

- Timing depends on which signal is asserted last: CE, OE, IB, or UB.
 Timing depends on which signal is de-asserted first: CE, OE, IB, or UB.
- 3. tbob delay is required only in cases where the opposite port is completing a write operation to the same address location. For simultaneous read operations BUSY has no relation to valid output data.
- 4. Start of valid data depends on which timing becomes effective last tAOE, tACE, tAA or tBDD.
- 5. $\overline{\text{SEM}} = \text{VIH}.$
- 6. Refer to Chip Enable Truth Table.

AC Electrical Characteristics Over the

Operating Temperature and Supply Voltage^(5,6)

		70V27X15 Com'l Only		70V27X20 Com'l Only		70V27X25 Com'l Only		
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
WRITE CY	CLE							
twc	Write Cycle Time	15		20		25		ns
tew	Chip Enable to End-of-Write ⁽³⁾	12		15	—	20	—	ns
taw	Address Valid to End-of-Write	12	_	15	—	20		ns
tas	Address Set-up Time ⁽³⁾	0		0	—	0		ns
₩P	Write Pulse Width	12	_	15	_	20		ns
twr	Write Recovery Time	0		0		0		ns
tow	Data Valid to End-of-Write	10		15		15	—	ns
tHZ	Output High-Z Time (1.2)		10		10		15	ns
tDH	Data Hold Time ⁽⁴⁾	0	_	0	—	0		ns
twz	Write Enable to Output in High-Z (1.2)		10		10	_	15	ns
tow	Output Active from End-of-Write (1.2.4)	0	_	0	_	0		ns
tswrd	SEM Flag Write to Read Time	5	_	5	—	5		ns
tsps	SEM Flag Contention Window	5		5	—	5		ns

3603 tbl 13a

		70V27X35 Com'l & Ind		70V27X55 Com'l Only				
Symbol	Parameter	Min.	Мах.	Min.	Max.	Unit		
WRITE CYCLE								
twc	Write Cycle Time	35		55		ns		
tew	Chip Enable to End-of-Write ⁽³⁾	30		45		ns		
taw	Address Valid to End-of-Write	30		45		ns		
tas	Address Set-up Time ⁽³⁾	0		0		ns		
twp	Write Pulse Width	25		40	_	ns		
twr	Write Recovery Time	0		0	-	ns		
tow	Data Valid to End-of-Write	20		30		ns		
tHZ	Output High-Z Time ^(1,2)		20	_	25	ns		
tDH	Data Hold Time ⁽⁴⁾	0	_	0	_	ns		
twz	Write Enable to Output in High-Z ^(1,2)		20	-	25	ns		
tow	Output Active from End-of-Write (1.2.4)	0		0	_	ns		
tswrd	SEM Flag Write to Read Time	5		5		ns		
tsps	SEM Flag Contention Window	5		5		ns		
						3603 tbl 13b		

NOTES:

1. Transition is measured 0mV from Low or High-impedance voltage with Output Test Load (Figure 2).

2.

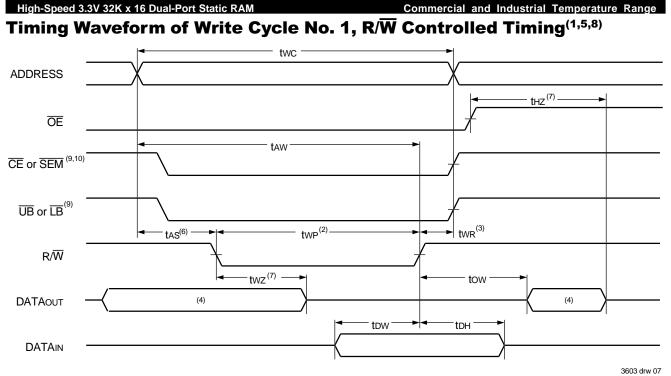
5. 'X' in part numbers indicates power rating (S or L).

6. Industrial temperature: for other speeds, packages and powers contact your sales office.

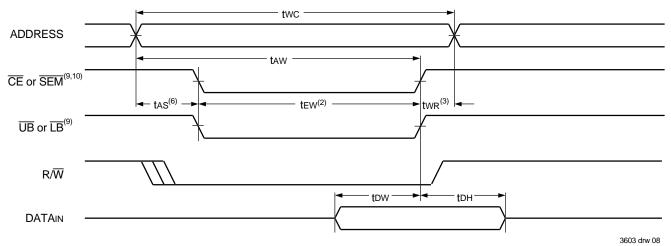
This parameter is guaranteed by device characterization, but is not production tested. To access RAM \overrightarrow{CE} = VIL and \overrightarrow{SEM} = VIL. To access semaphore, \overrightarrow{CE} = VIH and \overrightarrow{SEM} = VIL. Either condition must be valid for the entire tew time. Refer to Chip Enable 3. Truth Table.

^{4.} The specification for tDH must be met by the device supplying write data to the RAM under all operating conditions. Although tDH and tow values will vary over voltage and temperature, the actual tDH will always be smaller than the actual tow.

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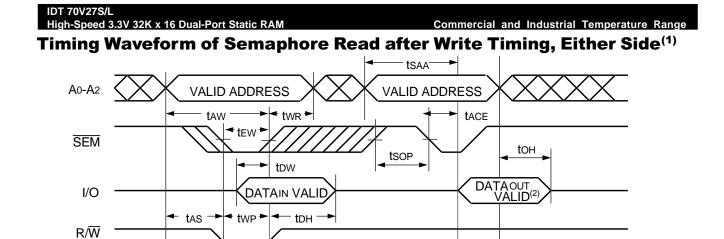
Timing Waveform of Write Cycle No. 2, CE, UB, LB Controlled Timing^(1,5)



NOTES:

- 1. R/W or \overline{CE} or \overline{UB} and \overline{LB} must be HIGH during all address transitions.
- 2. A write occurs during the overlap (tew or twp) of a LOW CE and a LOW R/W for memory array writing cycle.
- 3. twr is measured from the earlier of CE or R/W (or SEM or R/W) going HIGH to the end of write cycle.
- 4. During this period, the I/O pins are in the output state and input signals must not be applied.
- 5. If the CE or SEM LOW transition occurs simultaneously with or after the R/W LOW transition, the outputs remain in the High-impedance state.
- 6. Timing depends on which enable signal is asserted last, \overline{CE} or R/\overline{W} .
- 7. This parameter is guaranteed by device characterization, but is not production tested. Transition is measured 0mV from steady state with the Output Test Load (Figure 2).
- 8. If \overline{OE} is LOW during R/W controlled write cycle, the write pulse width must be the larger of twp or (twz + tow) to allow the I/O drivers to turn off and data to be placed on the bus for the required tow. If \overline{OE} is HIGH during an R/W controlled write cycle, this requirement does not apply and the write pulse can be as short as the specified twp.
- 9. To access RAM, CE = VIL and SEM = VIH. To access semaphore, CE = VIH and SEM = VIL. tew must be met for either condition.

10. Refer to Chip Enable Truth Table.



tSWRD

► taoe

3603 drw 09

Read Cycle

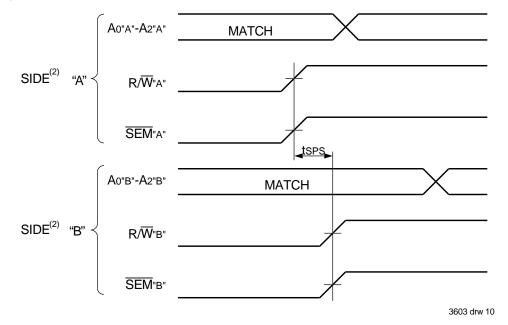
NOTES:

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- 1. $\overline{CE} = V_{IH}$ or \overline{UB} and $\overline{LB} = V_{IH}$ for the duration of the above timing (both write and read cycle), refer to Chip Enable Truth Table.
- 2. "DATAOUT VALID" represents all I/O's (I/Oo-I/O15) equal to the semaphore value.

Write Cycle

Timing Waveform of Semaphore Write Contention^(1,3,4)



NOTES:

- 1. DOR = DOL = VIL, $\overline{CE}R = \overline{CE}L = VIH$, or both $\overline{UB} \& \overline{LB} = VIH$ (refer to Chip Enable Truth Table).
- 2. All timing is the same for left and right ports. Port "A" may be either left or right port. Port "B" is the opposite from port "A".
- 3. This parameter is measured from RW*A* or SEM*A* going HIGH to R/W*B* or SEM*B* going HIGH.
- 4. If tsps is not satisfied, there is no guarantee which side will be granted the semaphore flag.

AC Electrical Characteristics Over the

Operating Temperature and Supply Voltage $Range^{(6,7)}$

			70V27X15 Com'l Only		70V27X20 Com'l Only		70V27X25 Com'l Only	
Symbol	Parameter	Min.	Мах.	Min.	Max.	Min.	Max.	Unit
BUSY TIMING (M/S=VIH)								
t BAA	BUSY Access Time from Address Match		15		20		25	ns
tBDA	BUSY Disable Time from Address Not Matched		15		20		25	ns
t BAC	BUSY Access Time from Chip Enable Low		15		20		25	ns
tbdc	BUSY Disable Time from Chip Enable High		15		20		25	ns
taps	Arbitration Priority Set-up Time ⁽²⁾			5		5		ns
tBDD	BUSY Disable to Valid Data ⁽³⁾		17	-	35		35	ns
twн	Write Hold After BUSY ⁽⁵⁾	12		15	-	20	-	ns
BUSY TIM	ING (M/Ŝ=VIL)							
twв	BUSY Input to Write ⁽⁴⁾	0		0	_	0	-	ns
twн	Write Hold After BUSY ⁽⁵⁾	12	-	15	_	20		ns
PORT-TO-	PORT DELAY TIMING				-		-	
twdd	Write Pulse to Data Delay ⁽¹⁾		30		45		55	ns
todd	Write Data Valid to Read Data Delay ⁽¹⁾		25		30	_	50	ns
								3603 tbl 14a

		-	35 Com'l Ind	70V27X55 Com'l Only			
Symbol	Parameter	Min.	Мах.	Min.	Max.	Unit	
BUSY TIM	ING (M/S=Vih)						
t BAA	BUSY Access Time from Address Match		35		45	ns	
tBDA	BUSY Disable Time from Address Not Matched		35		45	ns	
t BAC	BUSY Access Time from Chip Enable Low		35	_	45	ns	
tbdc	BUSY Disable Time from Chip Enable High		35		45	ns	
taps	Arbitration Priority Set-up Time ⁽²⁾	5		5		ns	
tBDD	BUSY Disable to Valid Data ⁽³⁾		40		50	ns	
twн	Write Hold After BUSY ⁽⁵⁾	25		25	_	ns	
BUSY TIM	ING (M/S=VIL)						
twв	BUSY Input to Write ⁽⁴⁾	0		0	_	ns	
twн	Write Hold After BUSY ⁽⁵⁾	25		25		ns	
PORT-TO-	PORT DELAY TIMING						
twdd	Write Pulse to Data Delay ⁽¹⁾	—	65		85	ns	
todd	Write Data Valid to Read Data Delay ⁽¹⁾	_	60		80	ns	
	•	-	•		•	3603 tbl 14b	

NOTES:

1. Port-to-port delay through RAM cells from writing port to reading port, refer to "Timing Waveform of Write with Port-to-Port Read and BUSY (M/S = VIH)".

2. To ensure that the earlier of the two ports wins.

3. tBDD is a calculated parameter and is the greater of 0, twDD - twp (actual), or tDDD - tDw (actual).

4. To ensure that the write cycle is inhibited on port "B" during contention on port "A".

5. To ensure that a write cycle is completed on port "B" after contention on port "A".

6. 'X' in part numbers indicates power rating (S or L).

7. Industrial temperature: for other speeds, packages and powers contact your sales office.

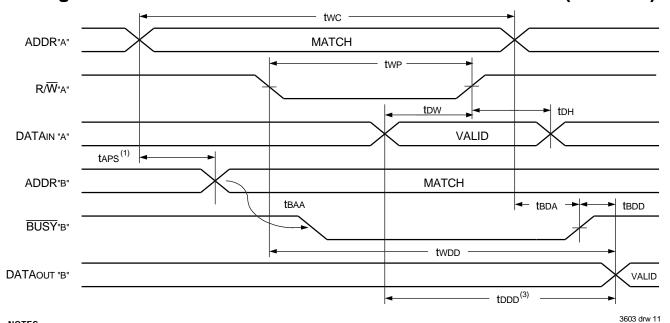
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High-Speed 3.3V 32K x 16 Dual-Port Static RAM

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Timing Waveform of Write with Port-to-Port Read and $\overline{\text{BUSY}}^{(2,5)}$ (M/ $\overline{\text{S}}$ = VIH)⁽⁴⁾



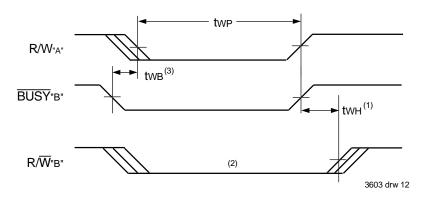
NOTES:

1. To ensure that the earlier of the two ports wins. taps is ignored for $M/\overline{S} = V_{IL}$ (SLAVE).

- 2. $\overline{CE}_{L} = \overline{CE}_{R} = V_{IL}$ (refer to Chip Enable Truth Table).
- 3. $\overline{OE} = V_{IL}$ for the reading port.
- 4. If M/S = VIL (SLAVE), then BUSY is an input. Then for this example BUSY "A"= VIH and BUSY "B"= input is shown above.

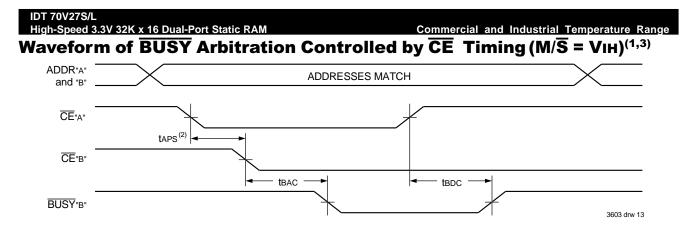
5. All timing is the same for left and right ports. Port "A" may be either the left or right port. Port "B" is the port opposite from port "A".

Timing Waveform Write with $\overline{\text{BUSY}}$ (M/ $\overline{\text{S}}$ = VIL)

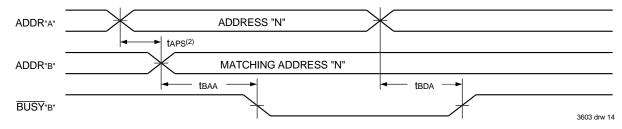


NOTES:

- 1. two must be met for both $\overline{\text{BUSY}}$ input (SLAVE) and output (MASTER).
- 2. BUSY is asserted on port "B" blocking R/W"B", until BUSY"B" goes HIGH.
- 3. twb is only for the "Slave" version.



Waveform of **BUSY** Arbitration Cycle Controlled by Address Match Timing $(M/S = VIH)^{(1)}$



NOTES:

1. All timing is the same for left and right ports. Port "A" may be either the left or right port. Port "B" is the port opposite from port "A".

2. If tAPS is not satisfied, the busy signal will be asserted on one side or another but there is no guarantee on which side busy will be asserted.

3. Refer to Chip Enable Truth Table.

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range^(1,2)

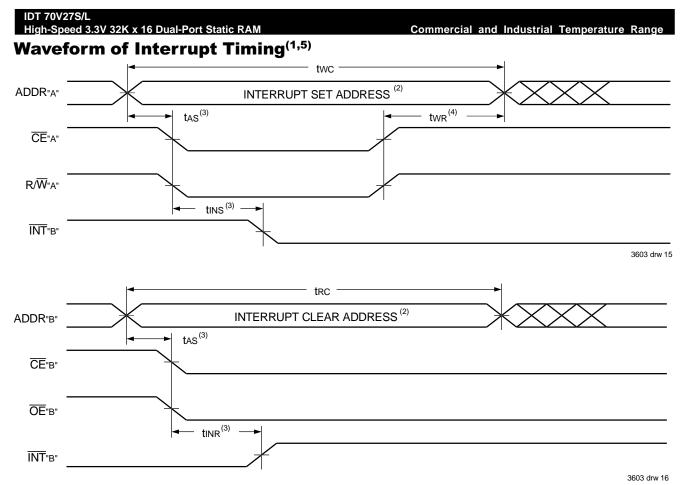
		70V27X15 Com'l Only		-	7X20 I'l Only	70V27X25 Com'l Only		
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
INTERRUP	T TIMING							
tas	Address Set-up Time	0		0		0		ns
tWR	Write Recovery Time	0		0		0		ns
tins	Interrupt Set Time		15		20	_	25	ns
tinr	Interrupt Reset Time		25		20		35	ns
							36	603 tbl 15a
				70V27X35 Com'l &Ind		70V27X55 Com'l Only		
Symbol	Parameter			Min.	Max.	Min.	Max.	Unit
INTERRUP	T TIMING							
tas	Address Set-up Time			0		0		ns
twr	Write Recovery Time			0		0		ns
tins	Interrupt Set Time				30		40	ns
tinr	Interrupt Reset Time				35		45	ns

NOTES:

1. 'X' in part numbers indicates power rating (S or L).

2. Industrial temperature: for other speeds, packages and powers contact your sales office.

3603 tbl 15b



NOTES:

1. All timing is the same for left and right ports. Port "A" may be either the left or right port. Port "B" is the port opposite from port "A".

2. See Interrupt Truth Table.

- 3. Timing depends on which enable signal (\overline{CE} or R/\overline{W}) is asserted last. 4. Timing depends on which enable signal (\overline{CE} or R/\overline{W}) is de-asserted first.
- 5. Refer to Chip Enable Truth Table.

	Left Port									
R/₩L	CE∟	OE L	A14L-A0L	ĪNT∟	R/Wr	CER	OE R	A14R-A0R	ĪNT	Function
L	L	Х	7FFF	Х	Х	Х	Х	х	L ⁽²⁾	Set Right INTR Flag
х	Х	Х	Х	Х	Х	Ĺ	Ĺ	7FFF	H ⁽³⁾	Reset Right INTR Flag
х	Х	Х	Х	L ⁽³⁾	L	L	Х	7FFE	Х	Set Left ĪNT∟ Flag
х	L	L	7FFE	H ⁽²⁾	Х	Х	Х	Х	Х	Reset Left INT∟ Flag

Truth Table IV — Interrupt Flag^(1,4)

NOTES:

1. Assumes $\overline{BUSY}_{L} = \overline{BUSY}_{R} = VIH$.

2. If $\overline{\text{BUSY}}_{L} = \text{VIL}$, then no change.

3. If $\overline{\text{BUSY}}_{R} = V_{IL}$, then no change.

4. Refer to Chip Enable Truth Table.

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Truth Table V — Address BUSY Arbritration⁽⁴⁾

	In	puts	Out	puts	
ĒĒ∟	CE R	A0L-A14L A0R-A14R	BUSYL ⁽¹⁾	BUSYR ⁽¹⁾	Function
Х	Х	NO MATCH	Н	Н	Normal
Н	Х	MATCH	Н	Н	Normal
Х	Н	MATCH	Н	Н	Normal
L	L	MATCH	(2)	(2)	Write Inhibit ⁽³⁾

NOTES:

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1. Pins BUSYL and BUSYR are both outputs when the part is configured as a master. Both are inputs when configured as a slave. BUSY outputs on the IDT70V27 are push-pull, not open drain outputs. On slaves the BUSY input internally inhibits writes.

2. "L" if the inputs to the opposite port were stable prior to the address and enable inputs of this port. "H" if the inputs to the opposite port became stable after the address and enable inputs of this port. If taps is not met, either BUSYL or BUSYR = LOW will result. BUSYL and BUSYR outputs can not be LOW simultaneously.

Writes to the left port are internally ignored when BUSYL outputs are driving LOW regardless of actual logic level on the pin. Writes to the right port are internally ignored when BUSYR outputs are driving LOW regardless of actual logic level on the pin.

4. Refer to Chip Enable Truth Table.

Truth Table VI — Example of Semaphore Procurement Sequence^(1,2)

Functions	D0 - D15 Left	Do - D15 Right	Status
No Action	1	1	Semaphore free
Left Port Writes "0" to Semaphore	0	1	Left port has semaphore token
Right Port Writes "0" to Semaphore	0	1	No change. Right side has no write access to semaphore
Left Port Writes "1" to Semaphore	1	0	Right port obtains semaphore token
Left Port Writes "0" to Semaphore	1	0	No change. Left port has no write access to semaphore
Right Port Writes "1" to Semaphore	0	1	Left port obtains semaphore token
Left Port Writes "1" to Semaphore	1	1	Semaphore free
Right Port Writes "0" to Semaphore	1	0	Right port has semaphore token
Right Port Writes "1" to Semaphore	1	1	Semaphore free
Left Port Writes "0" to Semaphore	0	1	Left port has semaphore token
Left Port Writes "1" to Semaphore	1	1	Semaphore free

NOTES:

1. This table denotes a sequence of events for only one of the eight semaphores on the IDT70V27.

2. There are eight semaphore flags written to via I/O0 and read from all the I/O's (I/O0-I/O15). These eight semaphores are addressed by A0 - A2.

Functional Description

The IDT70V27 provides two ports with separate control, address and I/O pins that permit independent access for reads or writes to any location in memory. The IDT70V27 has an automatic power down feature controlled by \overline{CE}_0 and CE1. The \overline{CE}_0 and CE1 control the on-chip power down circuitry that permits the respective port to go into a standby mode when not selected (\overline{CE} HIGH). When a port is enabled, access to the entire memory array is permitted.

Interrupts

If the user chooses the interrupt function, a memory location (mail box or message center) is assigned to each port. The left port interrupt flag (\overline{INT}_L) is asserted when the right port writes to memory location 7FFE (HEX), where a write is defined as $\overline{CE}_R = R/\overline{W}_R = VIL$ per the Truth Table IV. The left port clears the interrupt through access of address location

7FFE when $\overline{CE}_L = \overline{OE}_L = VIL$, R/ \overline{W} is a "don't care". Likewise, the right port interrupt flag (\overline{INTR}) is asserted when the left port writes to memory location 7FFF (HEX) and to clear the interrupt flag (\overline{INTR}), the right port must read the memory location 7FFF. The message (16 bits) at 7FFE or 7FFF is user-defined since it is an addressable SRAM location. If the interrupt func-tion is not used, address locations 7FFE and 7FFF are not used as mail boxes, but as part of the random access memory. Refer to Truth Table IV for the interrupt operation.

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Busy Logic

Busy Logic provides a hardware indication that both ports of the RAM have accessed the same location at the same time. It also allows one of the two accesses to proceed and signals the other side that the RAM is "Busy". The BUSY pin can then be used to stall the access until the operation on

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High-Speed 3.3V 32K x 16 Dual-Port Static RAM

the other side is completed. If a write operation has been attempted from the side that receives a **BUSY** indication, the write signal is gated internally to prevent the write from proceeding.

The use of BUSY logic is not required or desirable for all applications. In some cases it may be useful to logically OR the BUSY outputs together and use any BUSY indication as an interrupt source to flag the event of an illegal or illogical operation. If the write inhibit function of BUSY logic is not desirable, the BUSY logic can be disabled by placing the part in slave mode with the M/S pin. Once in slave mode the BUSY pin operates solely as a write inhibit input pin. Normal operation can be programmed by tying the BUSY pins HIGH. If desired, unintended write operations can be prevented to a port by tying the BUSY pin for that port LOW.

The BUSY outputs on the IDT 70V27 RAM in master mode, are pushpull type outputs and do not require pull up resistors to operate. If these RAMs are being expanded in depth, then the BUSY indication for the resulting array requires the use of an external AND gate.

Width Expansion with BUSY Logic Master/Slave Arrays

When expanding an IDT70V27 RAM array in width while using BUSY

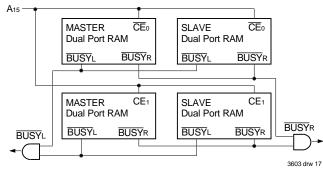


Figure 3. Busy and chip enable routing for both width and depth expansion with IDT70V27 RAMs.

logic, one master part is used to decide which side of the RAM array will receive a BUSY indication, and to output that indication. Any number of slaves to be addressed in the same address range as the master, use the busy signal as a write inhibit signal. Thus on the IDT70V27 RAM the BUSY pin is an output if the part is used as a master (M/S pin = VIH), and the BUSY pin is an input if the part is used as a slave (M/S pin = VIL) as shown in Figure 3.

If two or more master parts were used when expanding in width, a split decision could result with one master indicating BUSY on one side of the array and another master indicating BUSY on one other side of the array. This would inhibit the write operations from one port for part of a word and inhibit the write operations from the other port for the other part of the word.

The BUSY arbitration, on a master, is based on the chip enable and address signals only. It ignores whether an access is a read or write. In a master/slave array, both address and chip enable must be valid long enough for a BUSY flag to be output from the master before the actual write pulse can be initiated with either the RW signal or the byte enables. Failure to observe this timing can result in a glitched internal write inhibit signal and corrupted data in the slave.

Semaphores

The IDT70V27 is a fast Dual-Port 32K x 16 CMOS Static RAM with

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an additional 8 address locations dedicated to binary semaphore flags. These flags allow either processor on the left or right side of the Dual-Port RAM to claim a privilege over the other processor for functions defined by the system designer's software. As an example, the semaphore can be used by one processor to inhibit the other from accessing a portion of the Dual-Port RAM or any other shared resource.

The Dual-Port RAM features a fast access time, and both ports are completely independent of each other. This means that the activity on the left port in no way slows the access time of the right port. Both ports are identical infunction to standard CMOS Static RAM and can be read from, or written to, at the same time with the only possible conflict arising from the simultaneous writing of, or a simultaneous READ/WRITE of, a non-semaphore location. Semaphores are protected against such ambiguous situations and may be used by the system program to avoid any conflicts in the non-semaphore portion of the Dual-Port RAM. These devices have an automatic power-down feature controlled by CE the Dual-Port RAM enable, and SEM, the semaphore enable. The CE and SEM pins control on-chip power down circuitry that permits the respective port to go into standby mode when not selected. This is the condition which is shown in Truth Table II where CE and SEM are both HIGH.

Systems which can best use the IDT70V27 contain multiple processors or controllers and are typically very high-speed systems which are software controlled or software intensive. These systems can benefit from a performance increase offered by the IDT70V27's hardware semaphores, which provide a lockout mechanism without requiring complex programming.

Software handshaking between processors offers the maximum in system flexibility by permitting shared resources to be allocated in varying configurations. The IDT70V27 does not use its semaphore flags to control any resources through hardware, thus allowing the system designer total flexibility in system architecture.

An advantage of using semaphores rather than the more common methods of hardware arbitration is that wait states are never incurred in either processor. This can prove to be a major advantage in very highspeed systems.

How the Semaphore Flags Work

The semaphore logic is a set of eight latches which are independent of the Dual-Port RAM. These latches can be used to pass a flag, or token, from one port to the other to indicate that a shared resource is in use. The semaphores provide a hardware assist for a use assignment method called "Token Passing Allocation." In this method, the state of a semaphore latch is used as a token indicating that shared resource is in use. If the left processor wants to use this resource, it requests the token by setting the latch. This processor then verifies its success in setting the latch by reading it. If it was successful, it proceeds to assume control over the shared resource. If it was not successful in setting the latch, it determines that the right side processor has set the latch first, has the token and is using the shared resource. The left processor can then either repeatedly request that semaphore's status or remove its request for that semaphore to perform another task and occasionally attempt again to gain control of the token via the set and test sequence. Once the right side has relinguished the token, the left side should succeed in gaining control.

The semaphore flags are active low. A token is requested by writing a zero into a semaphore latch and is released when the same side writes

a one to that latch.

The eight semaphore flags reside within the IDT70V27 in a separate memory space from the Dual-Port RAM. This address space is accessed by placing a low input on the \overline{SEM} pin (which acts as a chip select for the semaphore flags) and using the other control pins (Address, \overline{OE} , and R/\overline{W}) as they would be used in accessing a standard Static RAM. Each of the flags has a unique address which can be accessed by either side through address pins A0 – A2. When accessing the semaphores, none of the other address pins has any effect.

When writing to a semaphore, only data pin Do is used. If a low level is written into an unused semaphore location, that flag will be set to a zero on that side and a one on the other side (see Table VI). That semaphore can now only be modified by the side showing the zero. When a one is written into the same location from the same side, the flag will be set to a one for both sides (unless a semaphore request from the other side is pending) and then can be written to by both sides. The fact that the side which is able to write a zero into a semaphore flags useful in interprocessor communications. (A thorough discussion on the use of this feature follows shortly.) A zero written into the same location from the semaphore is freed by the first side.

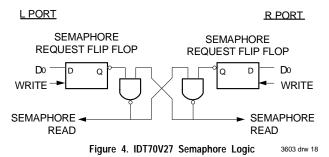
When a semaphore flag is read, its value is spread into all data bits so that a flag that is a one reads as a one in all data bits and a flag containing a zero reads as all zeros. The read value is latched into one side's output register when that side's semaphore select (SEM) and output enable (\overline{OE}) signals go active. This serves to disallow the semaphore from changing state in the middle of a read cycle due to a write cycle from the other side. Because of this latch, a repeated read of a semaphore in a test loop must cause either signal (\overline{SEM} or \overline{OE}) to go inactive or the output will never change.

A sequence WRITE/READ must be used by the semaphore in order to guarantee that no system level contention will occur. A processor requests access to shared resources by attempting to write a zero into a semaphore location. If the semaphore is already in use, the semaphore request latch will contain a zero, yet the semaphore flag will appear as a one, a fact which the processor will verify by the subsequent read (see Table VI). As an example, assume a processor writes a zero to the left port at a free semaphore location. On a subsequent read, the processor will verify that it has written successfully to that location and will assume control over the resource in question. Meanwhile, if a processor on the right side attempts to write a zero to the same semaphore flag it will fail, as will be verified by the fact that a one will be read from that semaphore on the right side during the subsequent read. Had a sequence of READ/WRITE been used instead, system contention problems could have occurred during the

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gap between the read and write cycles.

It is important to note that a failed semaphore request must be followed by either repeated reads or by writing a one into the same location. The reason for this is easily understood by looking at the simple logic diagram of the semaphore flag in Figure 4. Two semaphore request latches feed

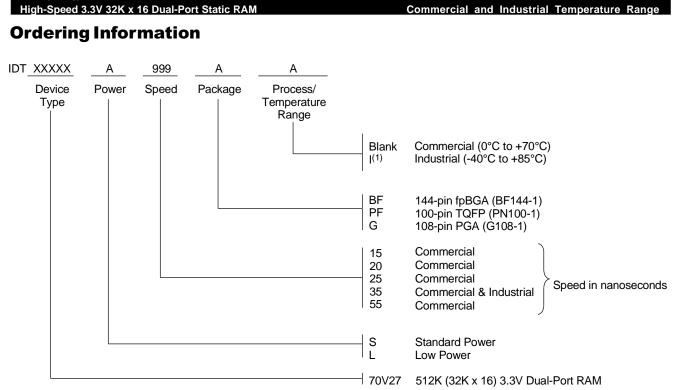


into a semaphore flag. Whichever latch is first to present a zero to the semaphore flag will force its side of the semaphore flag low and the other side high. This condition will continue until a one is written to the same semaphore request latch. Should the other side's semaphore request latch have been written to a zero in the meantime, the semaphore flag will flip over to the other side as soon as a one is written into the first side's request latch. The second side's flag will now stay low until its semaphore request latch is requested and the processor which requested it no longer needs the resource, the entire system can hang up until a one is written into that semaphore request latch.

The critical case of semaphore timing is when both sides request a single token by attempting to write a zero into it at the same time. The semaphore logic is specially designed to resolve this problem. If simultaneous requests are made, the logic guarantees that only one side receives the token. If one side is earlier than the other in making the request, the first side to make the request will receive the token. If both requests arrive at the same time, the assignment will be arbitrarily made to one port or the other.

One caution that should be noted when using semaphores is that semaphores alone do not guarantee that access to a resource is secure. As with any powerful programming technique, if semaphores are misused or misinterpreted, a software error can easily happen.

Initialization of the semaphores is not automatic and must be handled via the initialization program at power-up. Since any semaphore request flag which contains a zero must be reset to a one, all semaphores on both sides should have a one written into them at initialization from both sides to assure that they will be free when needed.



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NOTE:

IDT 70V27S/L

1. Industrial temperature range is available on selected TQFP packages in low power. For other speeds, packages and powers contact your sales office.

Preliminary Datasheet:

"PRELIMINARY' datasheets contain descriptions for products that are in early release.

High-Speed 3.3V 32K x 16 Dual-Port Static RAM

Datasheet Document History

12/3/98:	Initiated Document History
	Converted to new format
	Typographical and cosmetic changes
	Added fpBGA information
	Added 15ns and 20ns speed grades
	Updated DC Electrical Characteristics
	Added additional notes to pin configurations
4/2/99:	Page 5 Fixed typo in Table III
8/1/99:	Page 3 Changed package body height from 1.1mm to 1.4mm
8/30/99:	Page 1 Changed 660mW to 660µW
4/25/00:	Replaced IDT logo
	Page 2 Made pin correction
	Changed ±200mV to 0mV in notes
1/12/01:	Page 1 Fixed page numbering; copywright
	Page 6 Increated storage temperature parameter
	Clarified TA Parameter
	Page 7 and 8 DC Electrical parameters-changed wording from "open" to "disabled"
	Removed Preliminary status



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